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10/560,704	12/13/2005	Takefumi Nishimuta	5000-5296 9335		
	7590 10/22/2007 FINNEGAN, L.L.P.				
3 WORLD FIN	IANCIAL CENTER		QUACH, TUAN N		
NEW YORK, NY 10281-2101			ART UNIT	PAPER NUMBER	
		·	. 2826		
	,		NOTIFICATION DATE	DELIVERY MODE	
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Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

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•	Applica	ition No.	Applicant(s)			
	10/560,	,704	NISHIMUTA ET AL.			
Office Action Summar	Y Examin	er	Art Unit			
	Tuan Qı		2826			
The MAILING DATE of this con Period for Reply	nmunication appears on t	he cover sheet with the	correspondence address			
A SHORTENED STATUTORY PERIOD WHICHEVER IS LONGER, FROM TO Extensions of time may be available under the property of the state of the st	HE MAILING DATE OF wisions of 37 CFR 1.136(a). In no s communication, num statutory period will apply and or reply will, by statute, cause the altoriths after the mailing date of this	THIS COMMUNICATION event, however, may a reply be to suit expire SIX (6) MONTHS from application to become ABANDON	DN. timely filed m the mailing date of this communication. JED (35 U.S.C. § 133).			
Status						
1) Responsive to communication(s) filed on <u>7/26/07</u> .					
2a) This action is FINAL	2b)⊠ This action is	non-final.				
, —						
Disposition of Claims						
4) ⊠ Claim(s) <u>1-6</u> is/are pending in tage 4a) Of the above claim(s) 5) □ Claim(s) is/are allowed. 6) ⊠ Claim(s) <u>1-6</u> is/are rejected. 7) □ Claim(s) is/are objected. 8) □ Claim(s) are subject to respect to respe	_ is/are withdrawn from o					
Application Papers						
9) The specification is objected to 10) The drawing(s) filed on 13 Dece Applicant may not request that an Replacement drawing sheet(s) inc 11) The oath or declaration is object.	ember 2005 is/are: a) \(\sime\) y objection to the drawing(s) luding the correction is requ	s) be held in abeyance. S uired if the drawing(s) is o	ee 37 CFR 1.85(a). Objected to. See 37 CFR 1.121(d).			
Priority under 35 U.S.C. § 119						
a) Acknowledgment is made of a cap a) All b) Some * c) None 1. Certified copies of the property of the property of the certified copies of the property of the certified copies of the certified copi	of: iority documents have be iority documents have be opies of the priority docu- rnational Bureau (PCT R	een received. een received in Applica ments have been recei Rule 17.2(a)).	ation No ved in this National Stage			
Attachment(s)		4) Interview Summa	_			
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Re Information Disclosure Statement(s) (PTO/S Paper No(s)/Mail Date 		Paper No(s)/Mail				

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DETAILED ACTION

Claims 1 and 6 are amended. Claims 7 and 8 have been cancelled.

Claims 1-6 are rejected under 35 U.S.C. 103(a) as being unpatentable over
Oikawa 6,316,998 B1 or Ogawa et al. 04-154312 taken with Hieda (2002/0011612) and
Sugawa et al. (EP 1347506) and further in view of Fitzgeral 2003/0057439 A1.

Re claims 1-6, Oikawa teaches a DC amplifier comprising a differential amplifier circuit including a MISFET transistor MP1 and MISFET transistor MP2. See Fig. 1, column 5 lines 4-36. Ogawa et al. also DC amplifer comprising differential circuit 1 . employing MISFET transistors Tr1-Tr5 as shown in Fig. 4 and the abstract. Thus either Oikawa or Ogawa lack primarily the showing of the MISFET having components as characterized and the selection of gate widths of the p channel and n channel MIS so that the current drive capabilities of the N-channel and of the P-channel MIS are substantially the same.

Hieda teaches MISFET transistor in which projection portion 13 is formed by a silicon substrate 10 having a first crystal surface as a primary surface and a second crystal surface as a side surface, a gate insulating film 18 on at least a part of a top surface and the side surface of the projecting portion 13, a gate 16 on the gate insulating film and source/drain 17 on both sides enclosing the gate insulating film. The various advantages include larger channel width, smaller planar surface area, improved carrier mobility, prevention of punch-through. The use of both n channel or p channel, e.g., as claimed in claim 6, is also shown, e.g., [0418], Figs. 48D, [0427] wherein CMOS

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circuit can be made. See Figs. 1-4, 12, 20, 33, 48, and the corresponding descriptions, particularly [0175]-[0182], [0501]-[0541].

Ogawa to have employed the MIS transistors in the above circuit since such devices have improved characteristics as taught by Hieda. Regarding the hydrogen removal from silicon surface using plasma, such correspond to a product by process limitation that does not impart patentability to the claims. It is well settled that a "product-by-process" claim is directed to the product per se, no matter how actually made. See *In re Thorpe et al.*, 227 USPQ 964 (CAFC, 1985) and the related case cited therein which make it clear that it is the final product per se which must be determined in a "product-by-process" claim, and not the patentability of the process, and that, as here, an old or obvious product produced by a new method is not patentable as a product, whether claimed in "product-by-process" claims or not. As stated in *Thorpe*,

Even though product-by-process claims are limited by and defined by the process, determination of patentability is based on the product itself. *In re Brown, 459 F.2d 531, 535, 173 USPQ 685, 688 (CCPA, 1972); In re Pilkington, 411 F.2d 1345, 1348, 162 USPQ 145, 147(CCPA 1969).*

When the prior art discloses a product which reasonably appears to be either identical with or only slightly different than a product claimed in a product-by-process claim, a rejection based alternatively on either section 102 or section 103 of the statute is eminently fair and acceptable. As a practical matter, the Patent Office is not equipped to manufacture products by the myriad of processes put before it and then obtain prior art products and make physical comparisons therewith." In re Brown, 459 F.2d 531, 535, 173 USPQ 685, 688 (CCPA 1972).

"The Patent Office bears a lesser burden of proof in making out a case of prima facie

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obviousness for product-by-process claims because of their peculiar nature" than when a product is claimed in the conventional fashion. In re Fessmann, 489 F.2d 742, 744, 180 USPQ 324, 326 (CCPA 1974). Once the examiner provides a rationale tending to show that the claimed product appears to be the same or similar to that of the prior art, although produced by a different process, the burden shifts to applicant to come forward with evidence establishing an unobvious difference between the claimed product and the prior art product. In re Marosi, 710 F.2d 798, 802, 218 USPQ 289, 292 (Fed. Cir. 1983)

Additionally, such hydrogen removal in plasma would have been conventional and obvious as evidenced by Sugawa et al. the abstract [0015]-[0023] to improve device characteristics including leakage current and break down current.

Regarding the amended recitation of the gate widths so that the current drive of the N channel and P channel device to be substantially the same would have been conventional and obivous in view of Fitzgerald 2003/0057439 A1, [0006]-[0011] which evidences that the NMOS and PMOS transistors can be designed to provide approximately equal driving capability by appropriately adjusting the widths of the gates, thereby permitting the balance of the respective current drives whereby device performance can be improved, e.g., [0011], including by widening the PMOS transistor, i.e., the width of the gate of the PMOS, [0008], to minimize stage delay.

Re claim 2, the channel width being a total width of top surface and of the side surface is apparent in the figures above given the positioning of the gate. Re claim 3, the respective surfaces are shown in the figures, including recitation of (100), .e.g., [0175], [0181]; and the (110) surface as the side surface would have been apparent or obvious given their orientation as shown in the figures.

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Re claims 4, and 5, the use of a third MIS MP3 to connect to source or drain of the first and second MIS MP1, MP2, as well as a fifth and sixth transistors is also shown in Fig. 1 of above in Oikawa and Fig. 4 of Ogawa wherein the respective constant current source and circuit would result. A recitation directed to the manner in which a claimed apparatus is intended to be used does not distinguish the claimed apparatus from the prior art – if the prior art has the capability to so perform. See MPEP 2114 and *Ex parte Masham*, 2 USPQ2d 1647 (1987). The recitation of a new intended use for an old product does not make a claim to that old product patentable. *In re Schreiber*, 44 USPQ2d 1429 (Fed. Cir. 1997)

Applicant's arguments with respect to claims 1-6 have been considered but are most in view of the new ground(s) of rejection.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to examiner Tuan Quach whose telephone number is 571-272-1717. The examiner can normally be reached on M-F from 8:30 AM to 4:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor Sue Purvis can be reached on 571-272-1236. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should

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Tuan Quach Primary Examiner